

Field Stop IGBT

650 V, 40 A

FGA40N65SMD

General Description

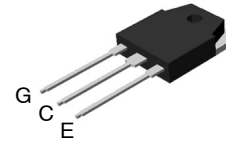
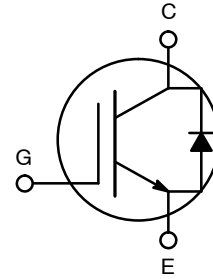
Using novel field stop IGBT technology, **onsemi**'s new series of field stop 2nd generation IGBTs offer the optimum performance for solar inverter, UPS, welder, induction heating, telecom, ESS and PFC applications where low conduction and switching losses are essential.

Features

- Maximum Junction Temperature: $T_J = 175^\circ\text{C}$
- Positive Temperature Co-efficient for Easy Parallel Operating
- High Current Capability
- Low Saturation Voltage: $V_{CE(sat)} = 1.9\text{ V (Typ.) @ } I_C = 40\text{ A}$
- Fast Switching: $E_{OFF} = 6.5\ \mu\text{J/A}$
- Tighten Parameter Distribution
- These Devices are Pb-Free and are RoHS Compliant

Applications

- Solar Inverter, UPS, Welder, Induction Heating
- Telecom, ESS



**TO-3P-3LD
CASE 340BZ**

MARKING DIAGRAM



FGA40N65SMD = Specific Device Code
 A = Assembly Location
 YWW = Date Code (Year & Week)
 ZZ = Assembly Lot

ORDERING INFORMATION

Device	Package	Shipping
FGA40N65SMD	TO-3P-3LD (Pb-Free)	450 Units / Tube

FGA40N65SMD

ABSOLUTE MAXIMUM RATINGS

Symbol	Description	Value	Unit
V_{CES}	Collector to Emitter Voltage	650	V
V_{GES}	Gate to Emitter Voltage	± 20	A
	Transient Gate to Emitter Voltage	± 30	A
I_C	Collector Current	@ $T_C = 25^\circ\text{C}$	80
	Collector Current	@ $T_C = 100^\circ\text{C}$	40
I_{CM} (Note 1)	Pulsed Collector Current	120	A
I_F	Diode Forward Current	@ $T_C = 25^\circ\text{C}$	40
	Diode Forward Current	@ $T_C = 100^\circ\text{C}$	20
I_{FM} (Note 1)	Pulsed Diode Maximum Forward Current	120	A
P_D	Maximum Power Dissipation	@ $T_C = 25^\circ\text{C}$	349
	Maximum Power Dissipation	@ $T_C = 100^\circ\text{C}$	174
T_J	Operating Junction Temperature	-55 to +175	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55 to +175	$^\circ\text{C}$
T_L	Maximum Lead Temp. for Soldering Purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: Pulse width limited by max. junction temperature.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta JC}$ (IGBT)	Thermal Resistance, Junction to Case, Max.	0.43	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$ (Diode)	Thermal Resistance, Junction to Case, Max.	1.5	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	40	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS OF THE DIODE ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
V_{FM}	Diode Forward Voltage	$I_F = 20\text{ A}$	$T_C = 25^\circ\text{C}$	-	2.1	2.6	V
			$T_C = 175^\circ\text{C}$	-	1.7	-	
E_{rec}	Reverse Recovery Energy	$I_F = 20\text{ A}$, $di_F/dt = 200\text{ A}/\mu\text{s}$	$T_C = 175^\circ\text{C}$	-	96	-	μJ
t_{rr}	Diode Reverse Recovery Time		$T_C = 25^\circ\text{C}$	-	42	-	ns
			$T_C = 175^\circ\text{C}$	-	200	-	
I_{rr}	Diode Peak Reverse Recovery Current		$T_C = 25^\circ\text{C}$	-	3.6	-	A
		$T_C = 175^\circ\text{C}$	-	8.0	-		
Q_{rr}	Diode Reverse Recovery Charge	$T_C = 25^\circ\text{C}$	-	76	-	nC	
		$T_C = 175^\circ\text{C}$	-	800	-		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

FGA40N65SMD

ELECTRICAL CHARACTERISTICS OF THE IGBT ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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OFF CHARACTERISTICS

BV_{CES}	Collector to Emitter Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 250\ \mu\text{A}$	650	–	–	V
$\Delta BV_{CES} / \Delta T_J$	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 250\ \mu\text{A}$	–	0.6	–	V/ $^\circ\text{C}$
I_{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0\text{ V}$	–	–	250	μA
I_{GES}	G–E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0\text{ V}$	–	–	± 400	nA

ON CHARACTERISTICS

$V_{GE(th)}$	G–E Threshold Voltage	$I_C = 250\ \mu\text{A}, V_{CE} = V_{GE}$	3.5	4.5	6.0	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 40\text{ A}, V_{GE} = 15\text{ V}$	–	1.9	2.5	V
		$I_C = 40\text{ A}, V_{GE} = 15\text{ V}, T_C = 175^\circ\text{C}$	–	2.1	–	V

DYNAMIC CHARACTERISTICS

C_{ies}	Input Capacitance	$V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	–	1880	–	pF
C_{oes}	Output Capacitance		–	180	–	pF
C_{res}	Reverse Transfer Capacitance		–	50	–	pF

SWITCHING CHARACTERISTICS

$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 400\text{ V}, I_C = 40\text{ A}, R_G = 6\ \Omega, V_{GE} = 15\text{ V},$ Inductive Load, $T_C = 25^\circ\text{C}$	–	12	16	ns
t_r	Rise Time		–	20	28	ns
$t_{d(off)}$	Turn-Off Delay Time		–	92	120	ns
t_f	Fall Time		–	13	17	ns
E_{on}	Turn-On Switching Loss		–	0.82	1.23	mJ
E_{off}	Turn-Off Switching Loss		–	0.26	0.34	mJ
E_{ts}	Total Switching Loss		–	1.08	1.57	mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 400\text{ V}, I_C = 40\text{ A}, R_G = 6\ \Omega, V_{GE} = 15\text{ V},$ Inductive Load, $T_C = 175^\circ\text{C}$	–	15	–	ns
t_r	Rise Time		–	22	–	ns
$t_{d(off)}$	Turn-Off Delay Time		–	116	–	ns
t_f	Fall Time		–	16	–	ns
E_{on}	Turn-On Switching Loss		–	1.08	–	mJ
E_{off}	Turn-Off Switching Loss		–	0.60	–	mJ
E_{ts}	Total Switching Loss		–	1.68	–	mJ
Q_g	Total Gate Charge	$V_{CE} = 400\text{ V}, I_C = 40\text{ A}, V_{GE} = 15\text{ V}$	–	119	180	nC
Q_{ge}	Gate to Emitter Charge		–	13	20	nC
Q_{gc}	Gate to Collector Charge		–	58	90	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL PERFORMANCE CHARACTERISTICS

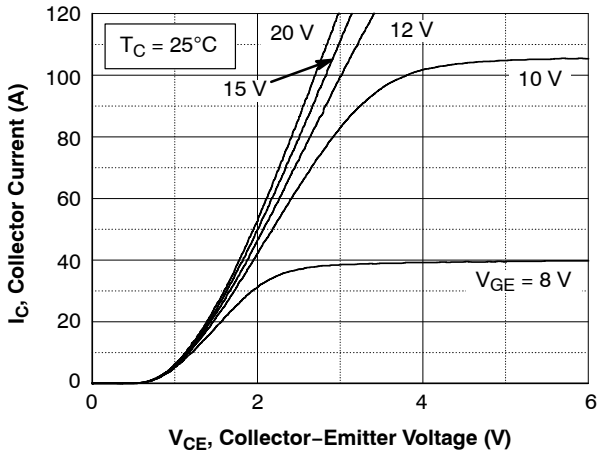


Figure 1. Typical Output Characteristics

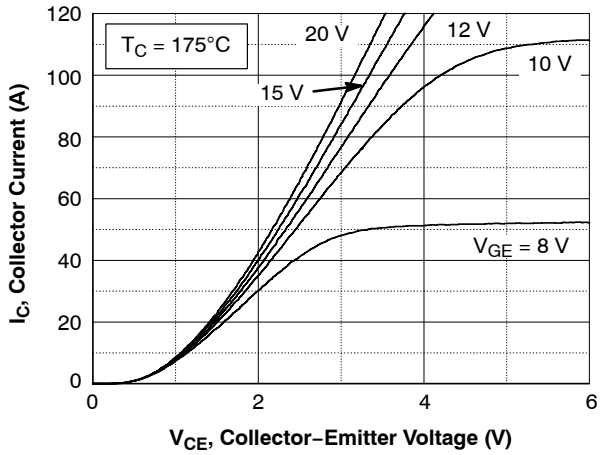


Figure 2. Typical Output Characteristics

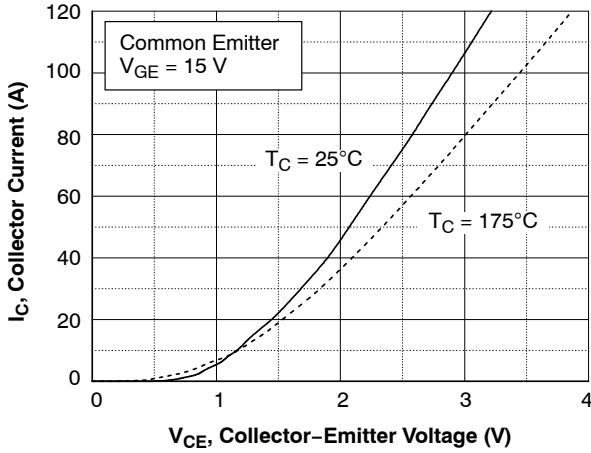


Figure 3. Typical Saturation Voltage Characteristics

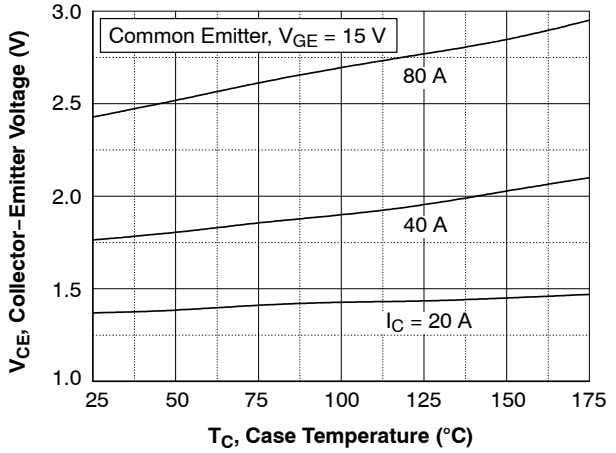


Figure 4. Saturation Voltage vs. Case Temperature at Variant Current Level

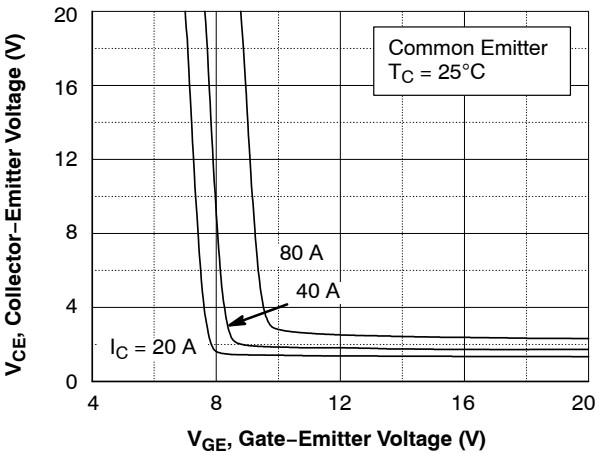


Figure 5. Saturation Voltage vs. V_{GE}

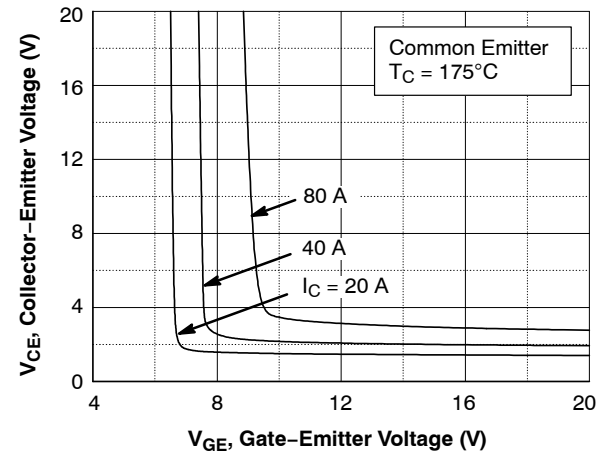


Figure 6. Saturation Voltage vs. V_{GE}

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

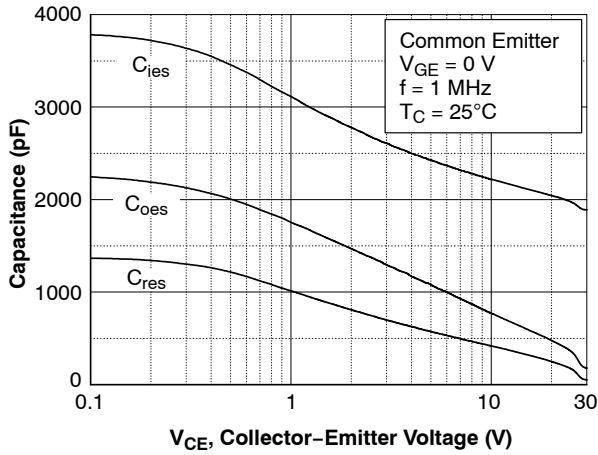


Figure 7. Capacitance Characteristics

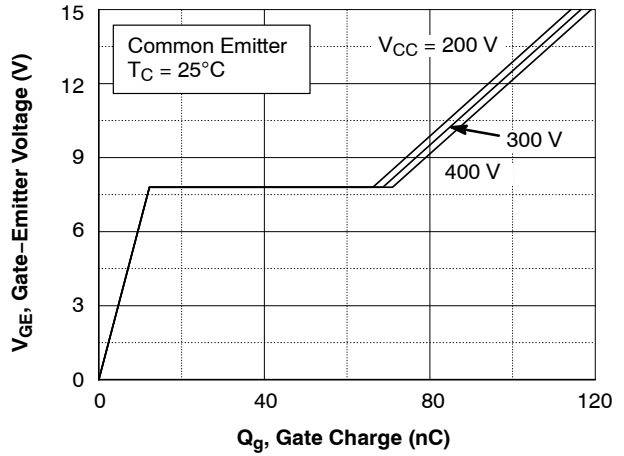


Figure 8. Gate Charge Characteristics

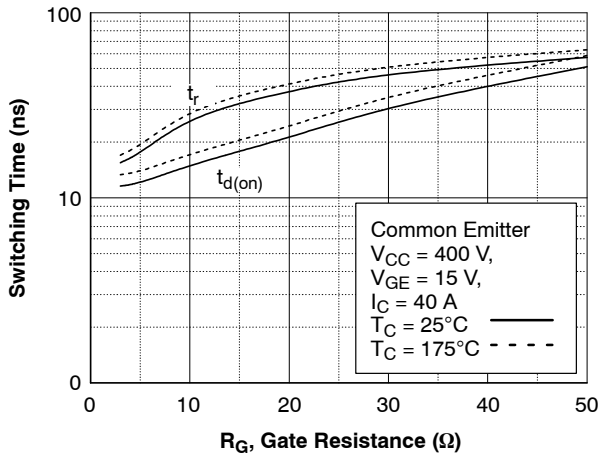


Figure 9. Turn-on Characteristics vs. Gate Resistance

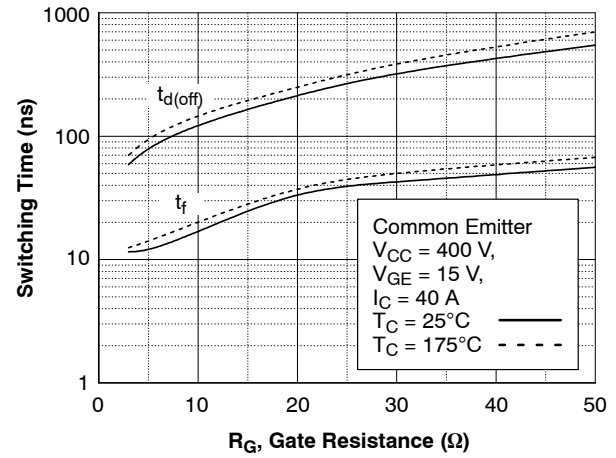


Figure 10. Turn-off Characteristics vs. Gate Resistance

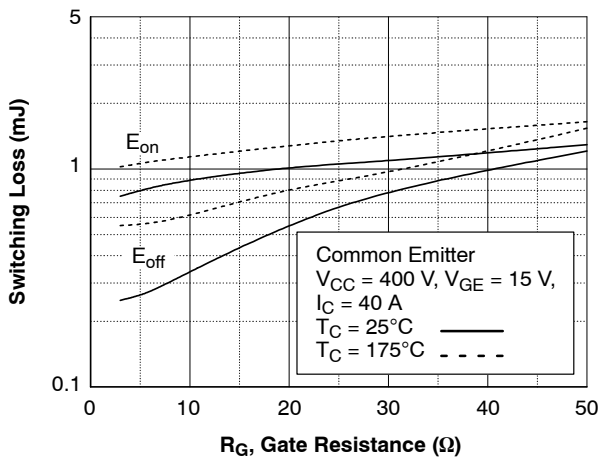


Figure 11. Switching Loss vs. Gate Resistance

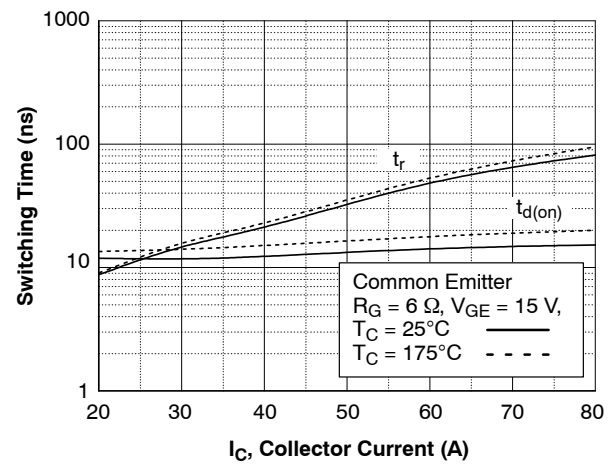


Figure 12. Turn-on Characteristics vs. Collector Current

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

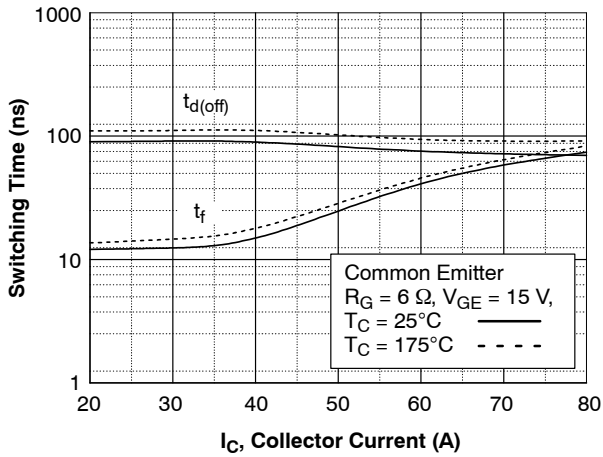


Figure 13. Turn-off Characteristics vs. Collector Current

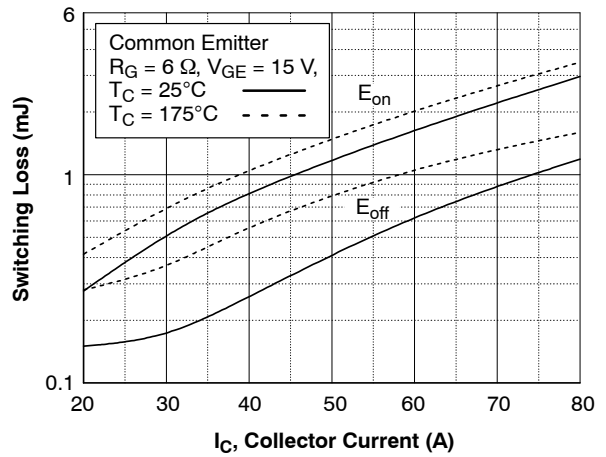


Figure 14. Switching Loss vs. Collector Current

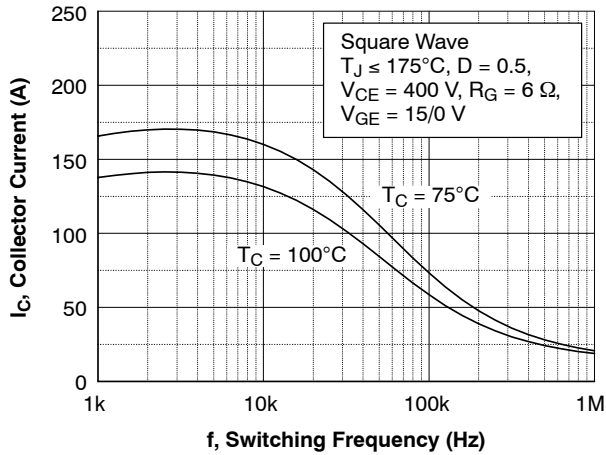


Figure 15. Load Current Vs. Frequency

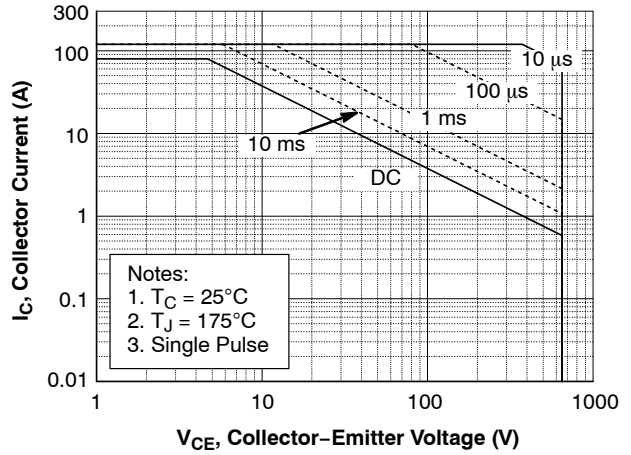


Figure 16. SOA Characteristics

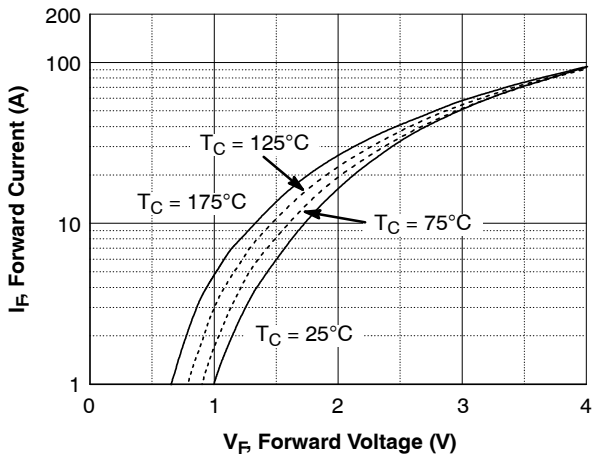


Figure 17. Forward Characteristics

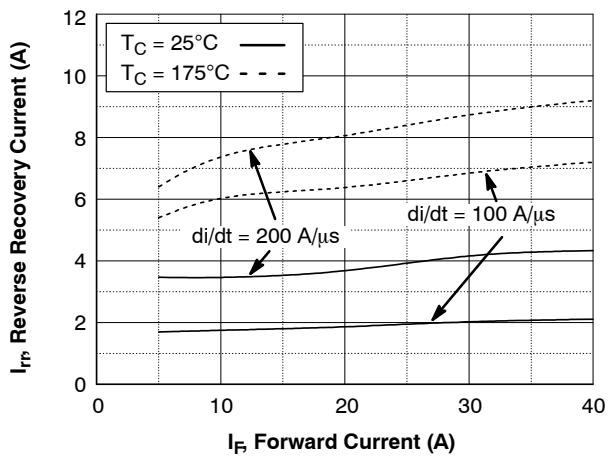


Figure 18. Reverse Recovery Current

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

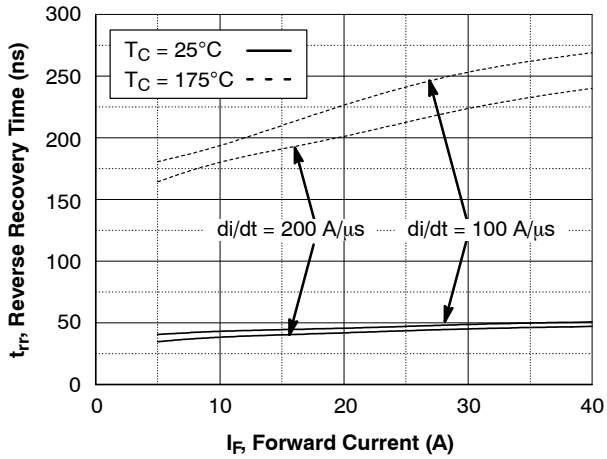


Figure 19. Reverse Recovery Time

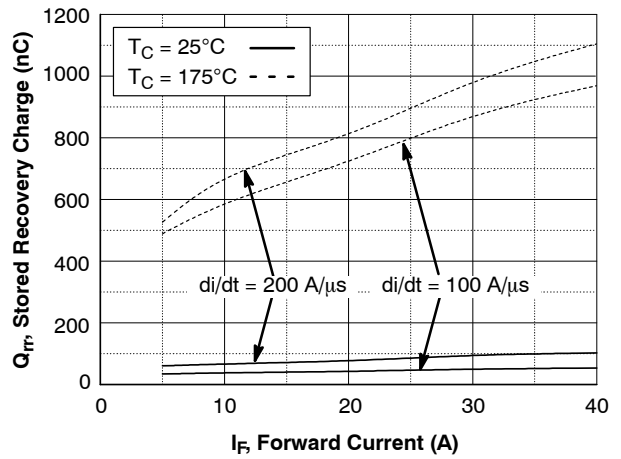


Figure 20. Stored Charge

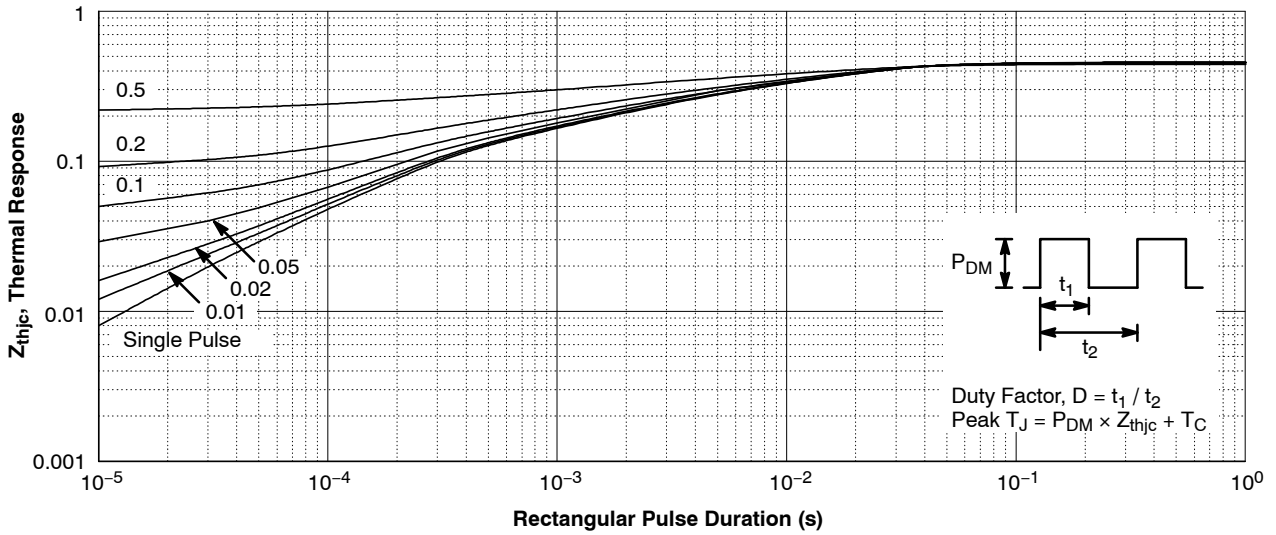


Figure 21. Transient Thermal Impedance of IGBT

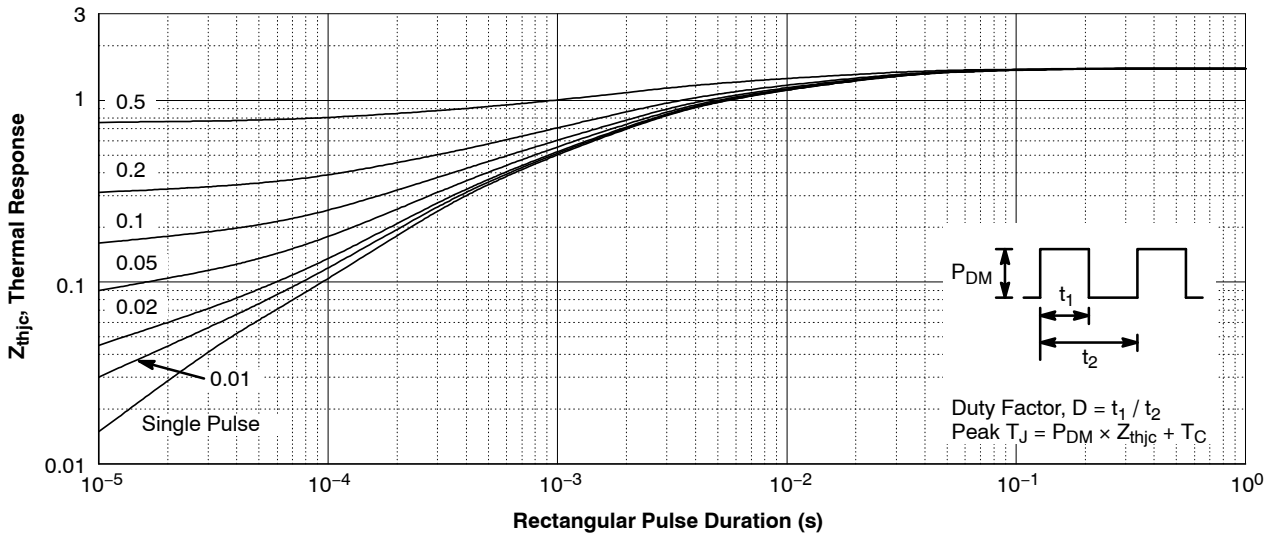


Figure 22. Transient Thermal Impedance of Diode

MECHANICAL CASE OUTLINE

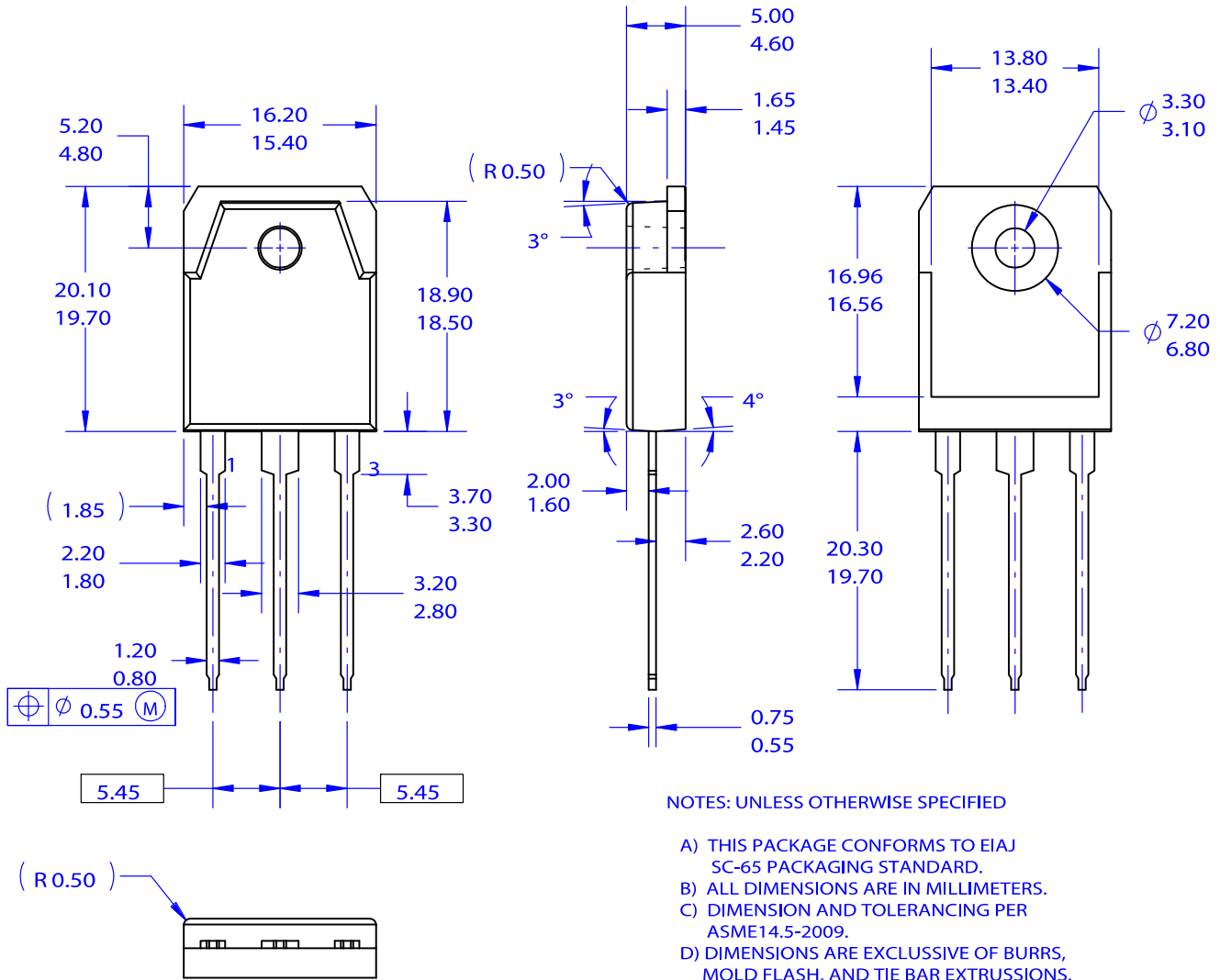
PACKAGE DIMENSIONS

ON Semiconductor®



TO-3P-3LD / EIAJ SC-65, ISOLATED CASE 340BZ ISSUE O

DATE 31 OCT 2016



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